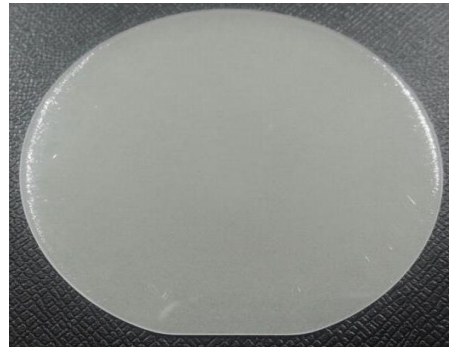


Epi - Wafer

AlN

Feature	AlN Epi. Wafer Single side polished (Growth surface)
Diameter	2" (50.8mm)
Thickness (Included substrate)	430 μ m \pm 15 μ m
Structure	AlN / Sapphire substrate



AlN on Sapphire Wafer

Characteristics (at 25°C)

Parameter	Typ.	Test Conditions	
Crack Free AlN Surface Area	Diameter >44mm		
Thickness	Thickness <3 μ m		
XRD	(002)	<200 arcsec	Panalytical HRXRD
	(102)	<400 arcsec	
RMS	2 μ m * 2 μ m	1 nm	

